

DIODE MODULE

DD200KB

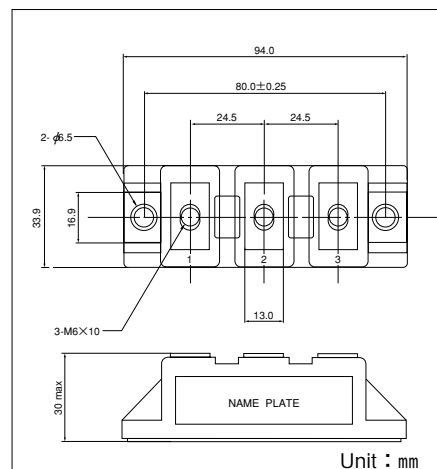
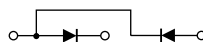
UL:E76102(M)

Power Diode Module **DD200KB** Series are designed for various rectifier circuits. **DD200KB** has two diode chips connected in series and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 1600V is available for various input voltages.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

- Various rectifiers, Battery chargers, DC motor drives



■ Maximum Ratings

(T_j=25°C unless otherwise specified)

Symbol	Item	Ratings				Unit
		DD200KB40	DD200KB80	DD200KB120	DD200KB160	
V _{RRM}	Repetitive Peak Reverse Voltage	400	800	1200	1600	V
V _{RSM}	Non-Repetitive Peak Reverse Voltage	480	960	1300	1700	V

Symbol	Item		Conditions	Ratings	Unit
I _{F(AV)}	Average Forward Current		Single phase, half wave, 180°C conduction, T _c =106°C	200	A
I _{F(RMS)}	R.M.S. Forward Current		Single phase, half wave, 180°C conduction, T _c =106°C	310	A
I _{FSM}	Surge Forward Current		1cycle, 50/60Hz, peak value, non-repetitive	5000/5500	A
I ² t	I ² t		Value for one cycle of surge current	125000	A ² S
T _j	Operating Junction Temperature			-40 to +150	°C
T _{stg}	Storage Temperature			-40 to +125	°C
V _{iso}	Isolation Breakdown Voltage (R.M.S.)		A.C. 1minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M6)	Recommended Value 2.5-3.9 (25-40)	4.7 (48)	
	Mass		Typical Value	240	g

■ Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I _{RRM}	Repetitive Peak Reverse Current, max.	T _j =150°C, V _R =V _{RRM}	50	mA
V _{FM}	Forward Voltage Drop, max.	T _j =25°C, I _F =620A	1.30	V
R _{th(j-c)}	Thermal Impedance, max.	Junction to case	0.17	°C/W

